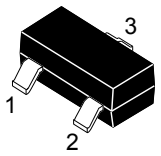
HI-SINCERITY
MICROELECTRONICS CORP.

HMBT2222AXLT1G

General Purpose Transistor NPN Silicon

Features

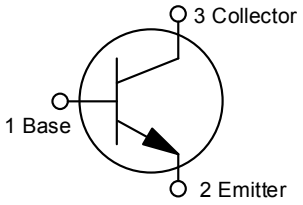
- RoHS Compliant and Halogen Free



SOT-23 (TO-236)

Ordering Information

Device	Marking	Shipping
HMBT2222AXLT1G	1P	3000/Tape & Reel



Maximum Ratings (T_A=25°C)

Parameter	Symbol	Limits	Units
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	75	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current-Continuous	I_C	600	mAdc

Thermal Characteristics

Parameter	Symbol	Limits	Units
Total Device Dissipation FR-5 Board[*1], T_A=25°C	P_D	225	mW
Total Device Dissipation, Derate above 25°C	P_D	1.8	mW/°C
Thermal Resistance, Junction to Ambient[*1]	$R_{\Theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate[*2], T_A=25°C	P_D	300	mW
Total Device Dissipation, Derate above 25°C	P_D	2.4	mW/°C
Thermal Resistance, Junction to Ambient	$R_{\Theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	°C

*1 FR-5=1.0x0.75x0.062 in
*2 Alumina=0.4x0.3x0.024 in. 99.5% alumina.

Electrical Characteristics (T_A=25°C)

Off Characteristics

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Collector-Emitter Breakdown Voltage (I_C=10mAdc, I_B=0)	$V_{(BR)CEO}$	40	-	-	V
Collector-Base Breakdown Voltage (I_C=10uAdc, I_E=0)	$V_{(BR)CBO}$	75	-	-	V
Emitter-Base Breakdown Voltage (I_E=10uAdc, I_C=0)	$V_{(BR)EBO}$	6	-	-	V
Collector Cutoff Current (V_{CE}=60Vdc, $V_{EB(off)}$=3.0Vdc)	I_{CEX}	-	-	10	nA
Collector Cutoff Current (V_{CB}=60V, I_E=0)	I_{CBO}	-	-	0.01	uA
Collector Cutoff Current (V_{CB}=60V, I_E=0, T_A=125°C)	I_{CBO}	-	-	10	uA
Emitter Cutoff Current (V_{EB}=3Vdc, I_C=0)	I_{EBO}	-	-	100	nA
Base Cutoff Current (V_{CE}=60Vdc, $V_{EB(off)}$=3.0Vdc)	I_{BL}	-	-	20	nA

On Characteristics

Characteristic	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain (I_C=0.1mAdc, V_{CE}=10Vdc)	hFE	35	-	-	-
DC Current Gain (I_C=1.0mAdc, V_{CE}=10Vdc)	hFE	50	-	-	-
DC Current Gain (I_C=10mAdc, V_{CE}=10Vdc)	hFE	75	-	-	-
DC Current Gain (I_C=10mAdc, V_{CE}=10Vdc, T_A=-55°C)	hFE	35	-	-	-
DC Current Gain (I_C=150mAdc, V_{CE}=10Vdc)*3	hFE	100	-	300	-
DC Current Gain (I_C=150mAdc, V_{CE}=1.0Vdc)*3	hFE	50	-	-	-
DC Current Gain (I_C=500mAdc, V_{CE}=10Vdc)*3	hFE	40	-	-	-
Collector-Emitter Saturation Voltage*3 (I_C=150mAdc, I_B=15mAdc)	$V_{CE(sat)}$	-	-	0.3	V
Collector-Emitter Saturation Voltage*3 (I_C=500mAdc, I_B=50mAdc)	$V_{CE(sat)}$	-	-	1	V
Base-Emitter Saturation Voltage (I_C=150mAdc, I_B=15mAdc)	$V_{BE(sat)}$	0.6	-	1.2	V
Base-Emitter Saturation Voltage (I_C=500mAdc, I_B=50mAdc)	$V_{BE(sat)}$	-	-	2	V

*3 Pulse Test: Pulse Width<300 μs, Duty Cycle<2.0%

Electrical Characteristics (T_A=25°C)

Small Signal Characteristics

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Current Gain Bandwidth Product*4 (I_C=20mAdc, V_{CE}=20Vdc, f=100MHz)	f_T	300	-	-	MHz
Output Capacitance (V_{CB}=10Vdc, I_E=0, f=1.0MHz)	C_{obo}	-	-	8	pF
Input Capacitance (V_{EB}=0.5Vdc, I_C=0, f=1.0MHz)	C_{ibo}	-	-	25	pF
Input Impedance (V_{CE}=10Vdc, I_C=10mAdc, f=1.0KHz)	h_{ie}	0.25	-	1.25	KΩ
Voltage Feedback Ratio (V_{CE}=10Vdc, I_C=10mAdc, f=1.0 kHz)	h_{re}	-	-	4	X10-4
Small–Signal Current Gain (V_{CE}=10Vdc, I_C=10mAdc, f=1.0KHz)	h_{fe}	75	-	375	
Output Admittance (V_{CE}=10Vdc, I_C=10mAdc, f=1.0KHz)	h_{oe}	25	-	200	umhos
Collector Base Time Constant (V_{CB}=20Vdc, I_E=20mAdc, f=31.8MHz)	rb, C_C	-	-	150	ps
Noise Figure (V_{CE}=10V, I_C=100μA, R_S=1.0KΩ , f =1.0KHz)	N_F	-	-	4	dB

Switching Characteristics

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Delay Time (V_{CC}=30Vdc, $V_{EB(off)}$=-0.5Vdc, I_C=150mAdc, I_{B1}=15mAdc)	td	-	-	10	ns
Rise Time (V_{CC}=30Vdc, $V_{EB(off)}$=-0.5Vdc, I_C=150mAdc, I_{B1}=15mAdc)	tr	-	-	25	ns
Storage Time (V_{CC}=30Vdc, I_C=150mAdc, I_{B1}=I_{B2}=15mAdc)	ts	-	-	225	ns
Fall Time (V_{CC}=30Vdc, I_C=150mAdc, I_{B1}=I_{B2}=15mAdc)	tf	-	-	60	ns

*4 f_T is defined as the frequency at which hfe extrapolates to unity.

Electrical Characteristics Curves

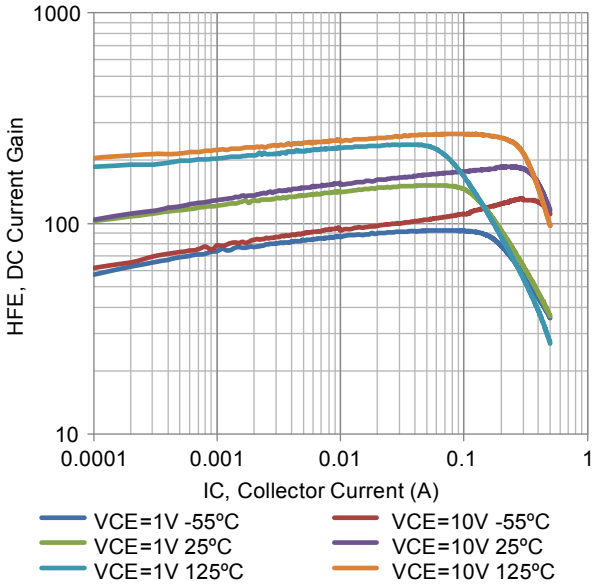


Figure1. DC Current Gain

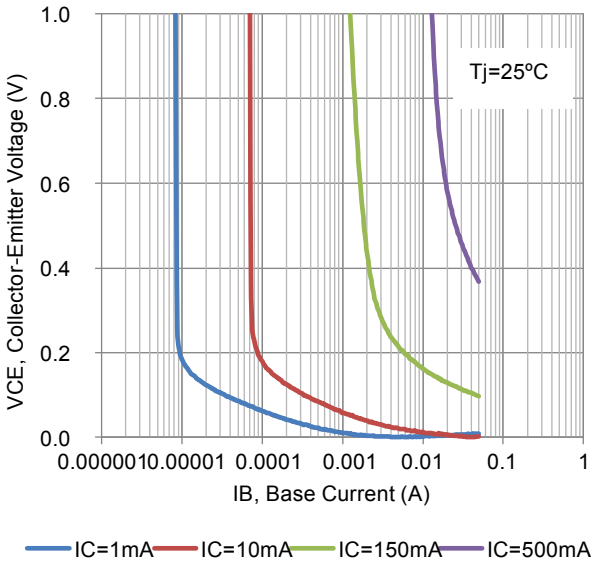


Figure 2. Collector Saturation Region

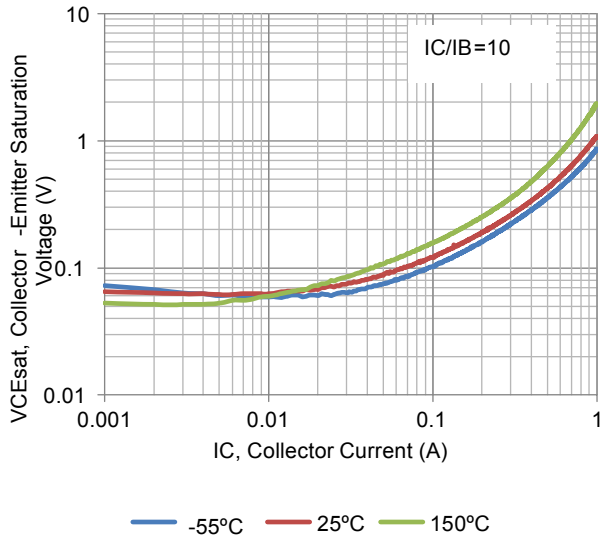


Figure 3. Collector Emitter Saturation Voltage vs. Collector Current

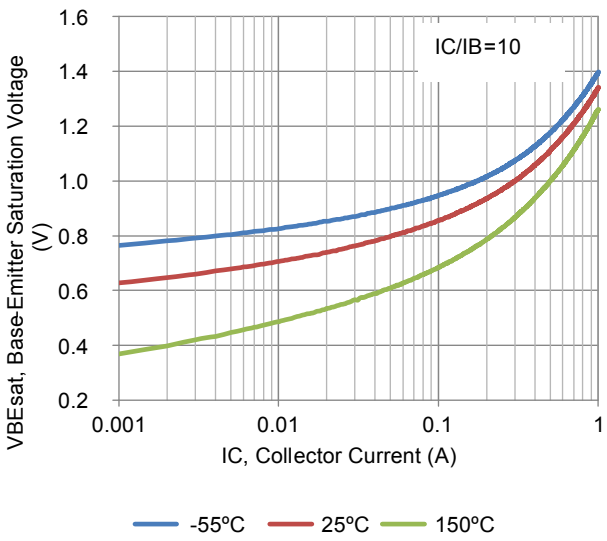


Figure 4. Base Emitter Saturation Voltage vs. Collector Current

Electrical Characteristics Curves

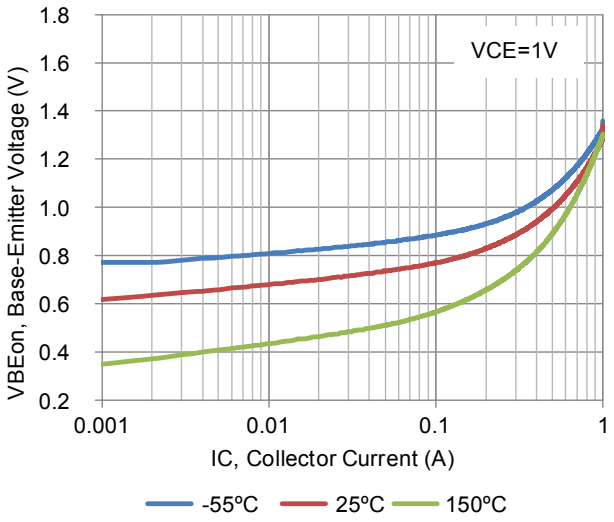


Figure 5. Base Emitter Voltage vs. Collector Current

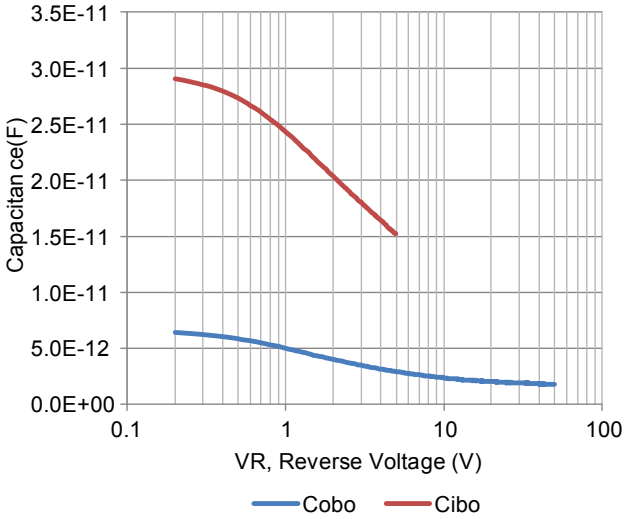


Figure 6. Capacitance

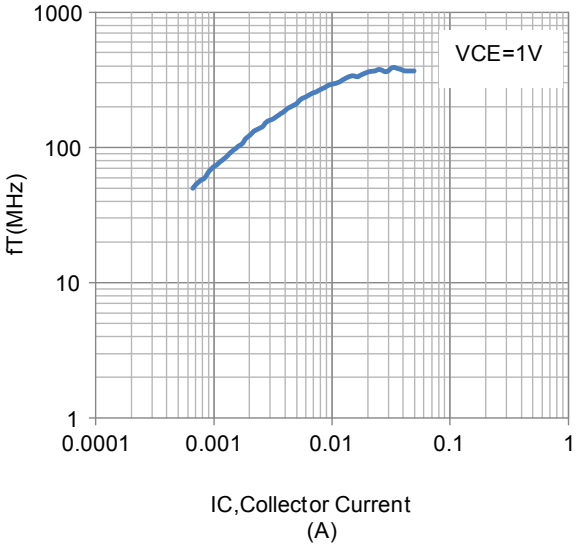
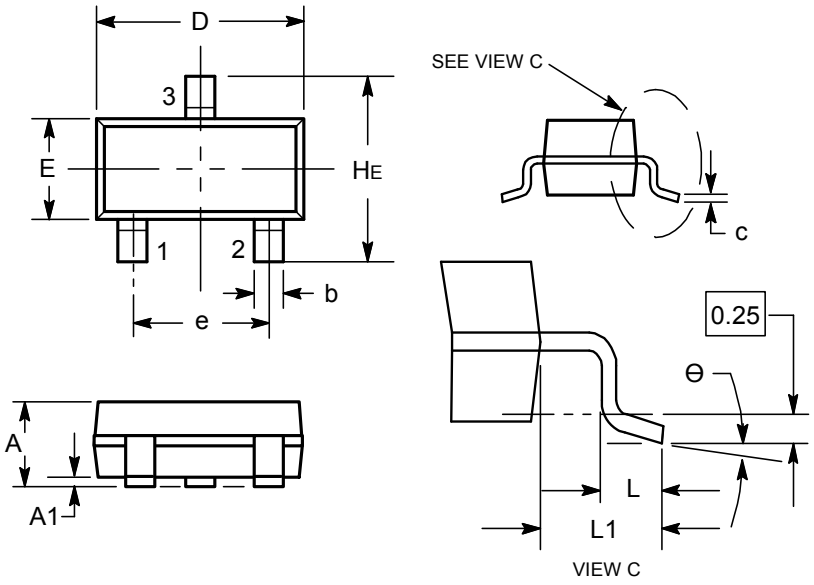


Figure 7. Current−Gain Bandwidth Product

Package Dimension



DIM	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	0.89	1	1.11	0.035	0.04	0.044
A1	0.01	0.06	0.1	0.001	0.002	0.004
b	0.37	0.44	0.5	0.015	0.018	0.02
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.9	3.04	0.11	0.114	0.12
E	1.20	1.3	1.4	0.047	0.051	0.055
e	1.78	1.9	2.04	0.07	0.075	0.081
L	0.10	0.2	0.3	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
H_E	2.10	2.4	2.64	0.083	0.094	0.104
θ	0^O	-	10^O	0^O	-	10^O

Notes:
1. Dimensioning and tolerancing per ansi Y14.5m, 1982.
2. Controlling Dimension: Millimeter.
3. Maximum lead thickness includes lead finish. Minimum lead thickness is the minimum thickness of base material.
4. Dimensions d and e do not include mold flash, protrusions or gate burrs.

Soldering Footprint